

N-Channel Enhancement Mode MOSFET

GENERAL DESCRIPTION

The PW2202 is silicon N-channel Enhanced VDMOSFETs, is obtained by the self-aligned planar Technology which reduce the conduction loss, improve switching performance and enhance the avalanche energy. The transistor can be used in various power switching circuit for system

FEATURES

VDS =200V, ID =2A

RDS(ON) < 1.8Ω @ VGS=10V

Available in a 3-Pin SOT23-3 Package

Application

LED dimming

Emergency lamp



Absolute Maximum Ratings (TA=25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	200	V
Gate-Source Voltage	V _{GS}	±20	V
Continuous Drain Current	I _{D@TA=25°C}	2	A
Pulsed Drain Current (NOTE1)	I _{DM}	10	A
Maximum Power Dissipation	P _D	3	W
Operating Junction and Storage Temperature Range	T _J , T _{STG}	-55 To 150	°C
Thermal Resistance Junction-Ambient (NOTE2)	R _{θJA}	41.7	°C/W

Note 1、Repetitive Rating: Pulse width limited by maximum junction temperature.

Note 2、Surface Mounted on FR4 Board, t ≤ 10 sec.



ELECTRICAL CHARACTERISTICS

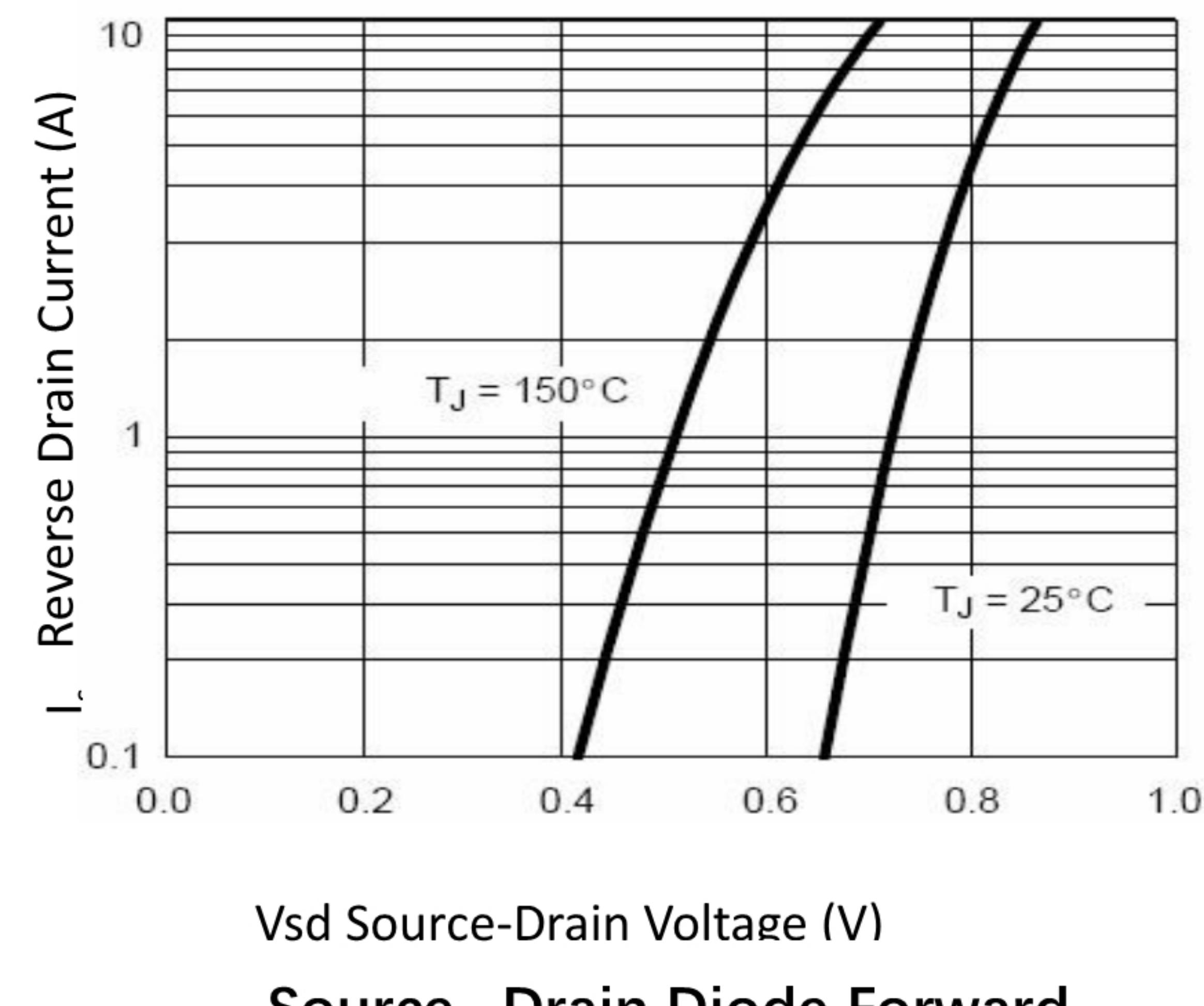
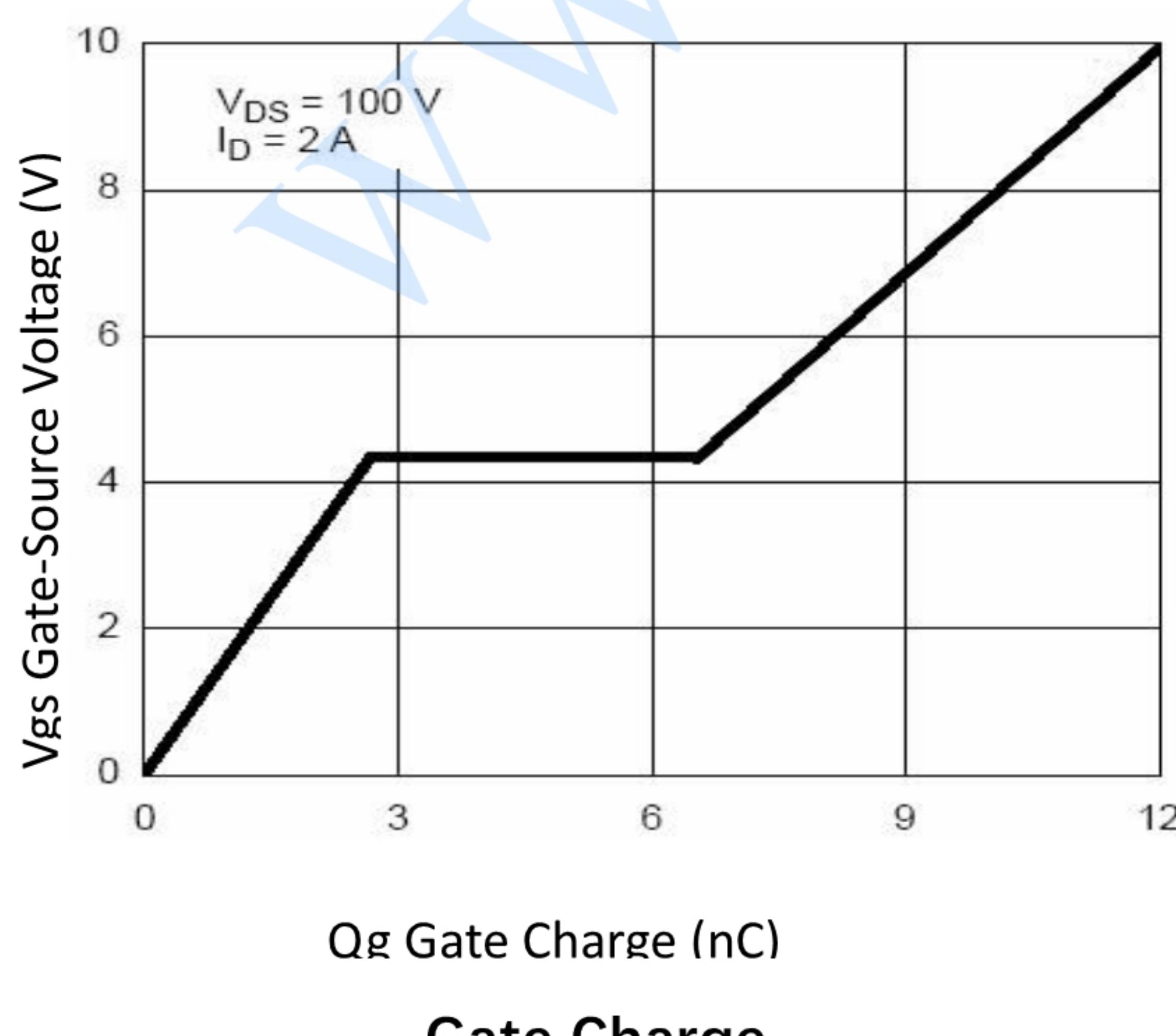
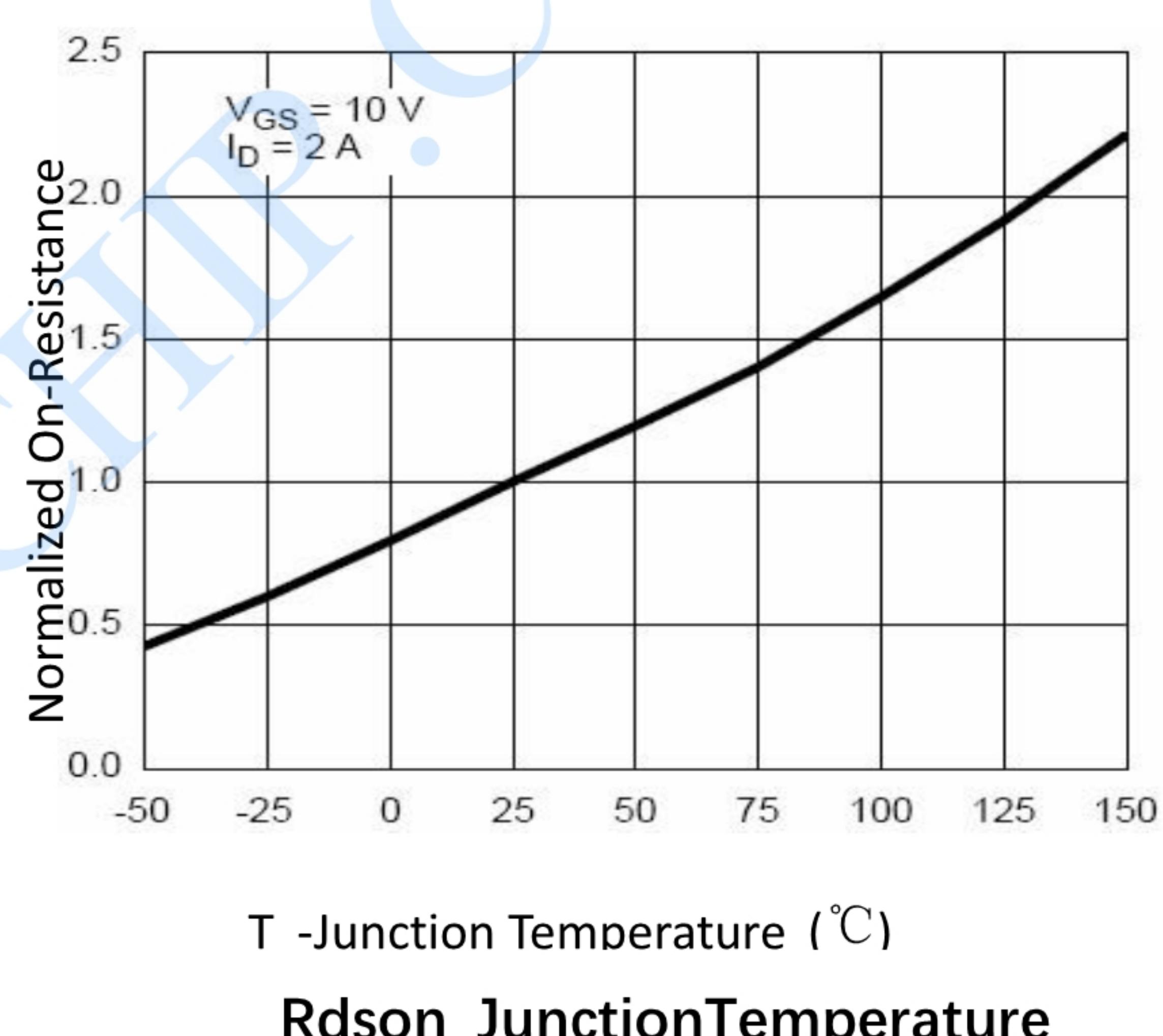
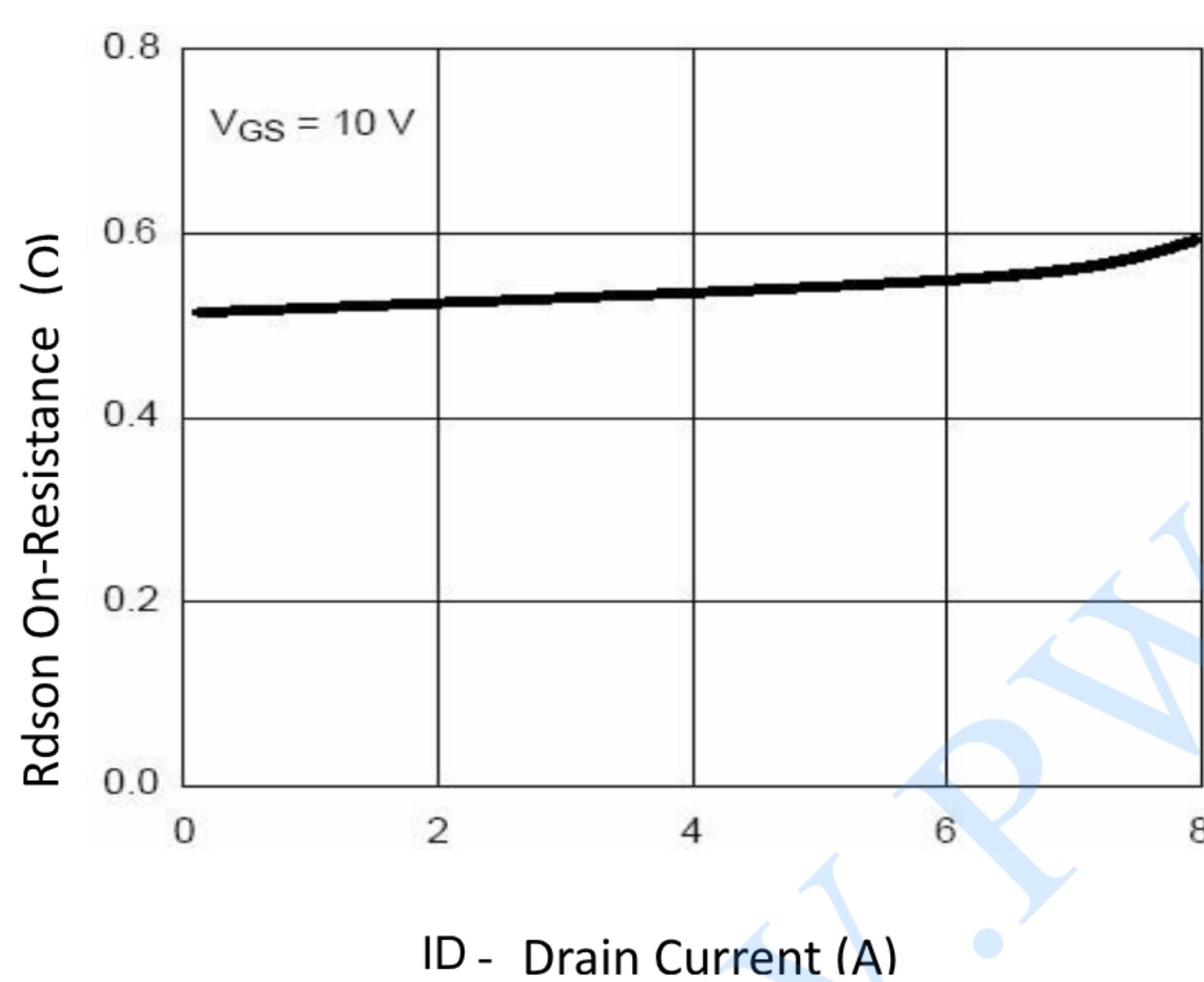
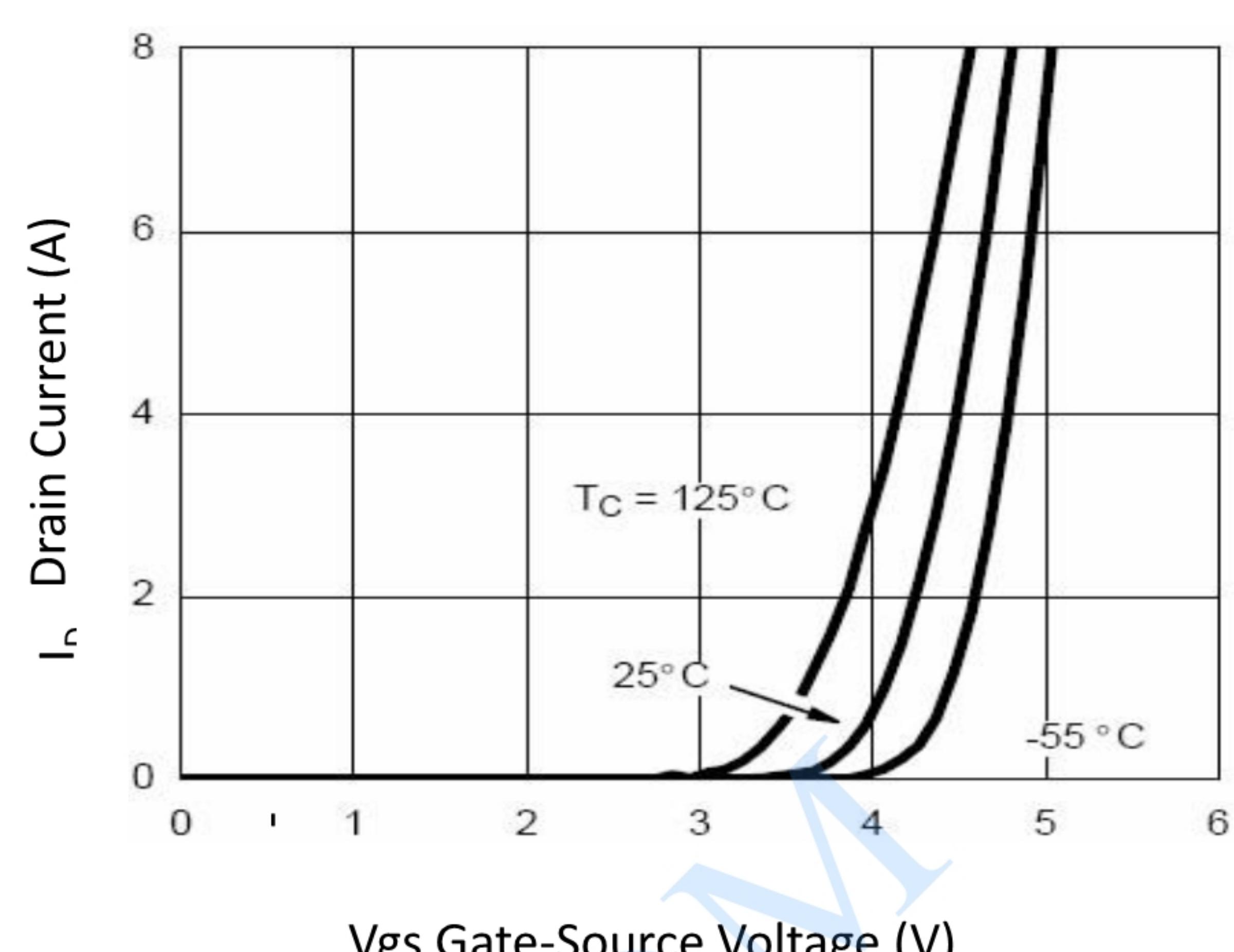
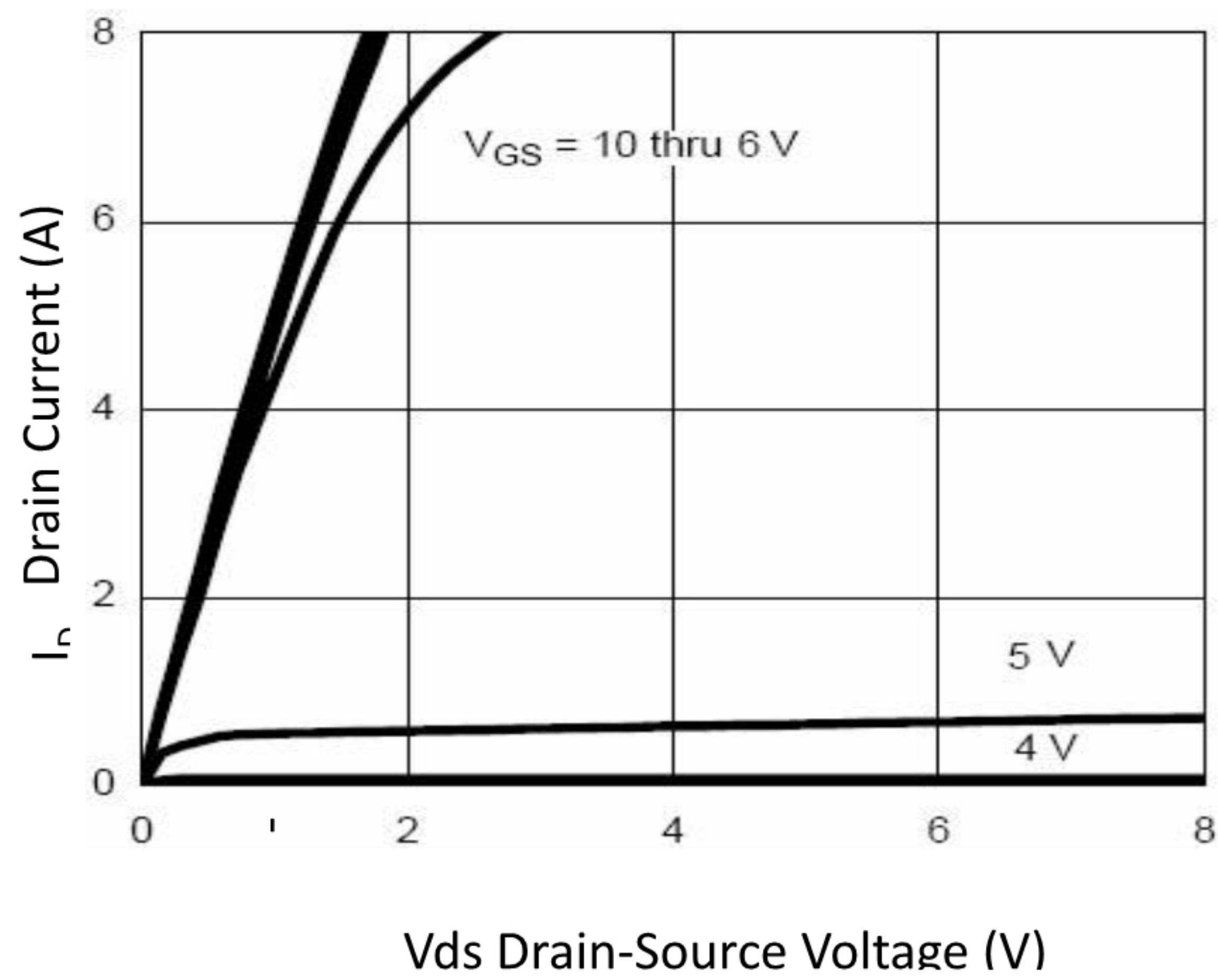
(TA = 25°C, unless otherwise noted.)

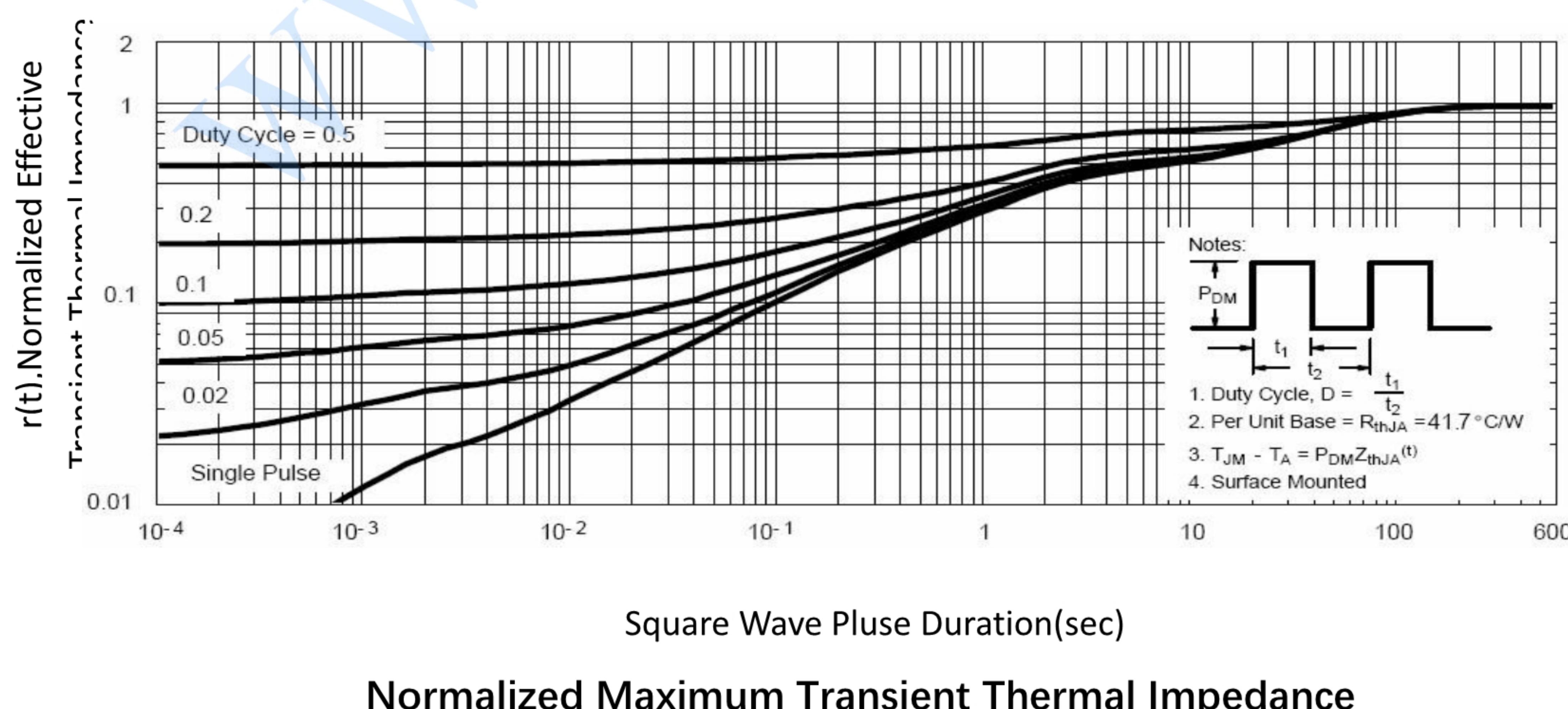
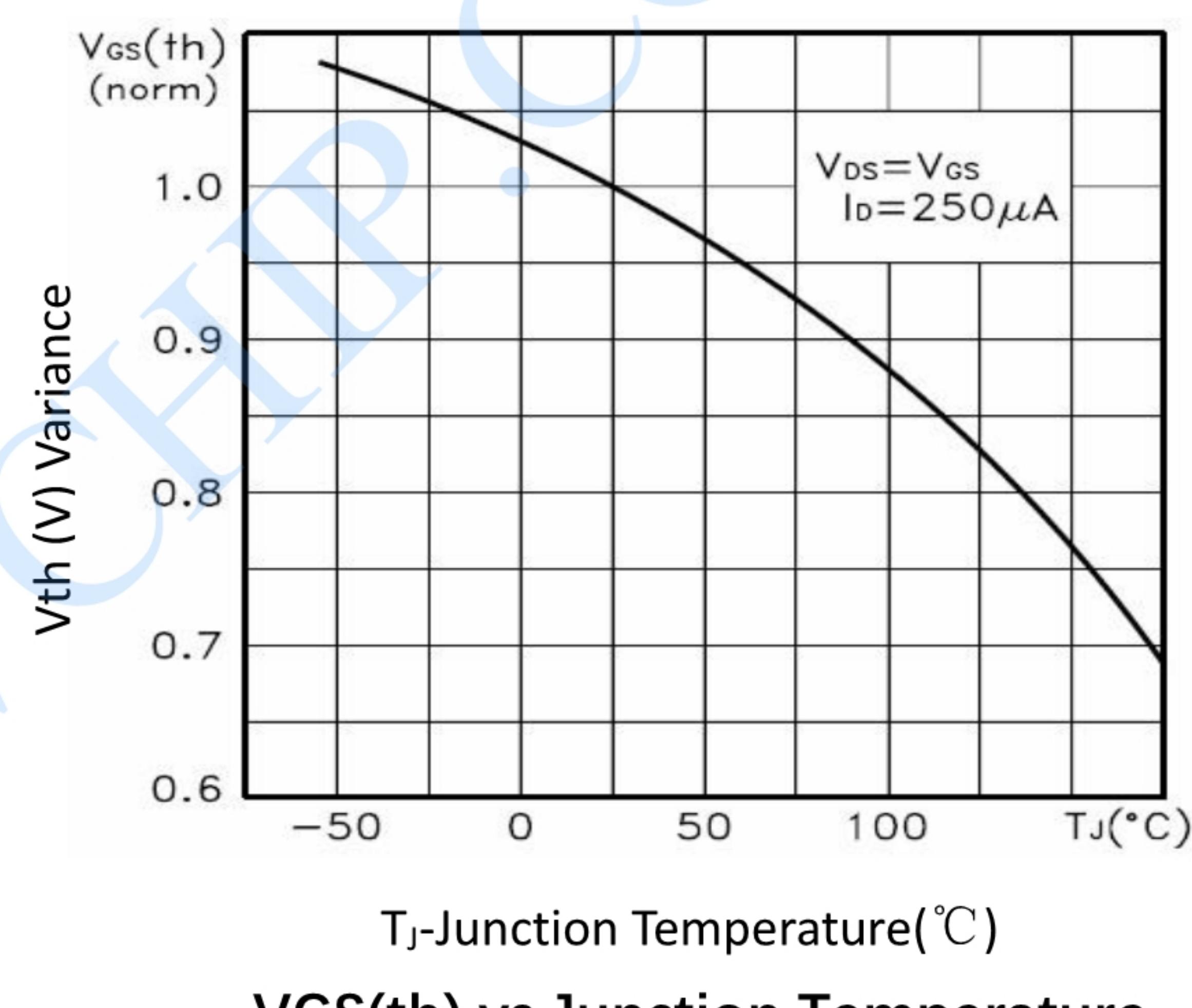
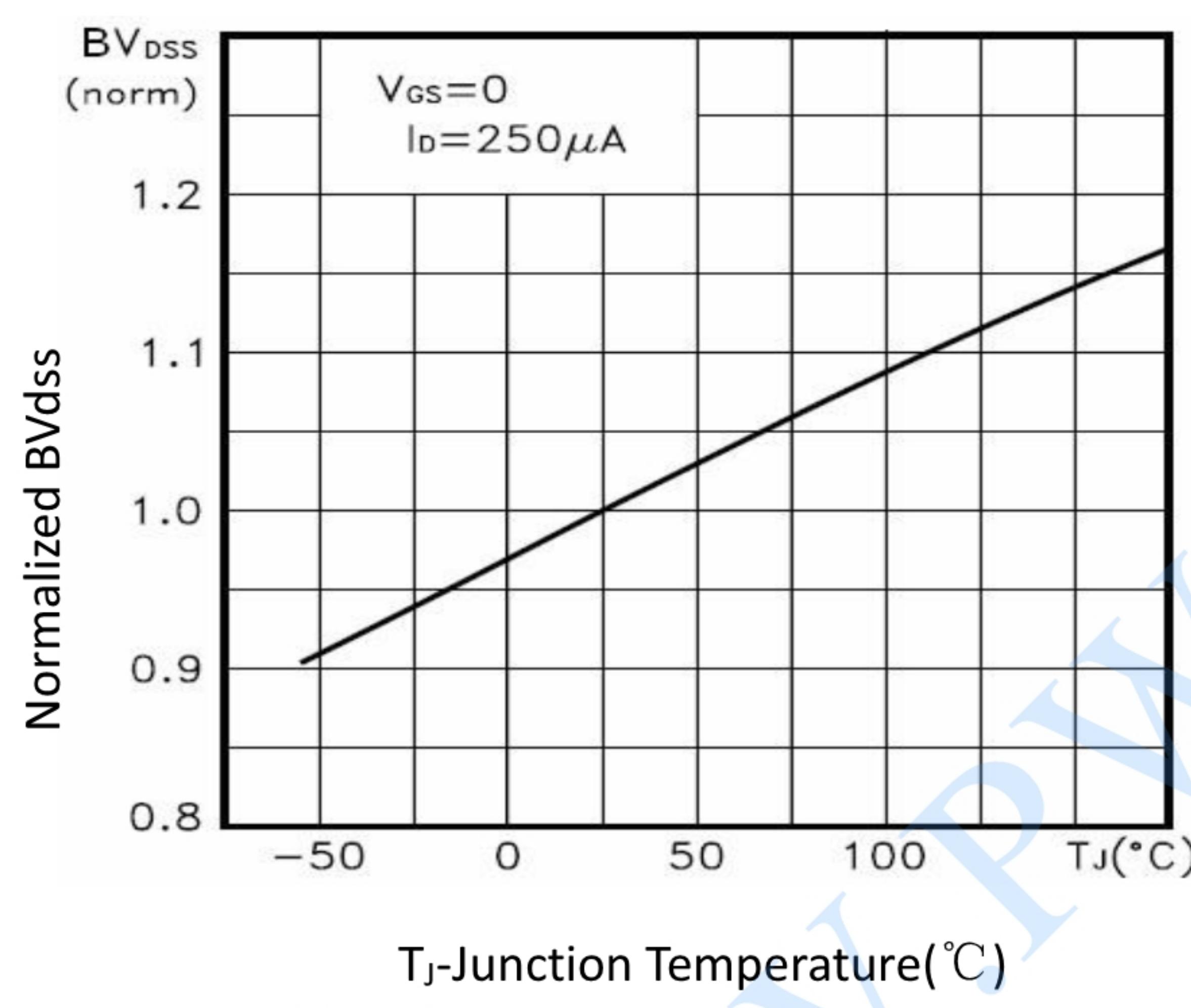
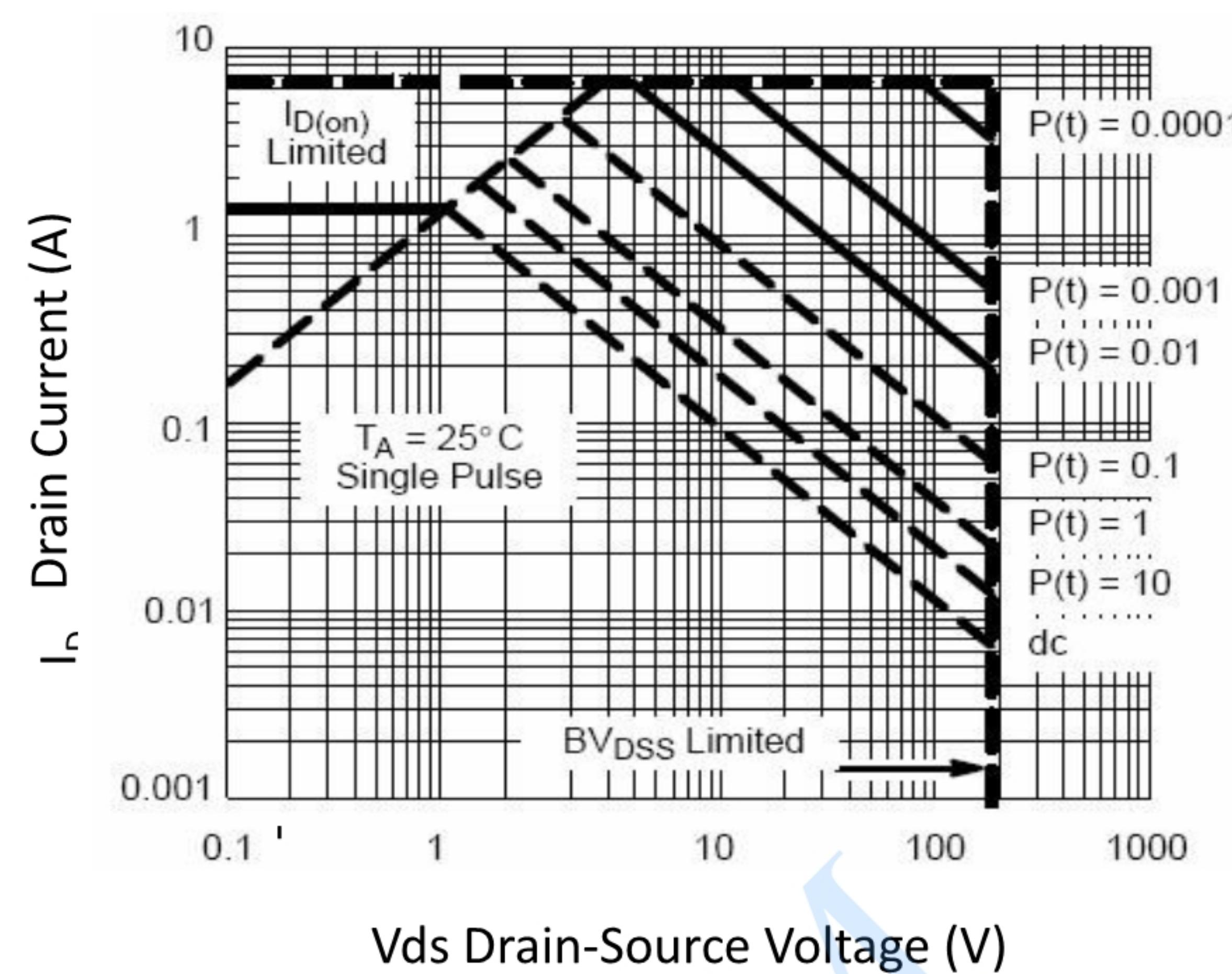
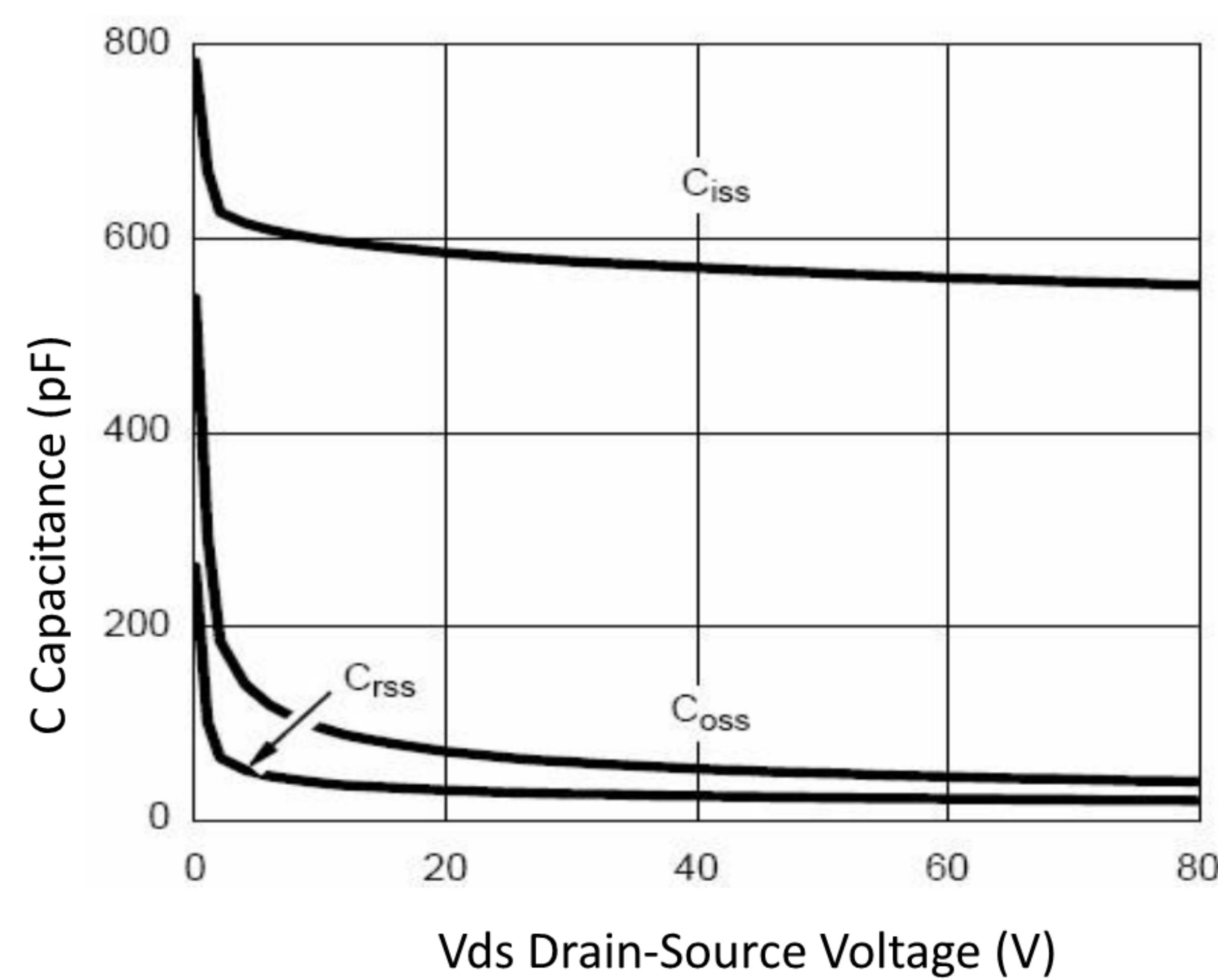
Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BVDSS	Drain-Source Breakdown Voltage	VGS=0V , ID=-250uA	200			V
RDS(ON)	Drain-Source On- Static Resistance	VGS=10V , ID=2A		1.4	1.8	Ω
VGS(th)	Gate Threshold Voltage	VGS=VDS , ID =-250uA	1.0		3.0	V
IDS	Zero Gate Voltage Drain Current	VDS=200V , VGS=0V ,			1	uA
IGSS	Gate-Body Leakage Current	VGS=±20V , VDS=0V			±100	nA
gfs	Forward Transconductance	VDS=15V , ID=2A		8		S
Qg	Total Gate Charge	VDS=100V , VGS=10V , ID=2A		12		nC
Qgs	Gate-Source Charge			2.5		nC
Qgd	Gate-Drain Charge			3.8		nC
Td(on)	Turn-On Delay Time	VDS=100V , VGS=10V , RG=2.5Ω, RL=15Ω		10		ns
Tr	Rise Time			12		ns
Td(off)	Turn-Off Delay Time			15		ns
Tf	Fall Time			15		ns
Ciss	Input Capacitance	VDS=25V , VGS=0V , f=1MHz		580		pF
Coss	Output Capacitance			90		pF
Crss	Reverse Transfer Capacitance			3		pF
Is	Continuous Source Current (NOTE1)				2	A
VSD	Diode Forward Voltage (NOTE2)	VGS=0V , Is=1A ,			1.2	V

Note 1. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%

Note 2. Guaranteed by design, not subject to production

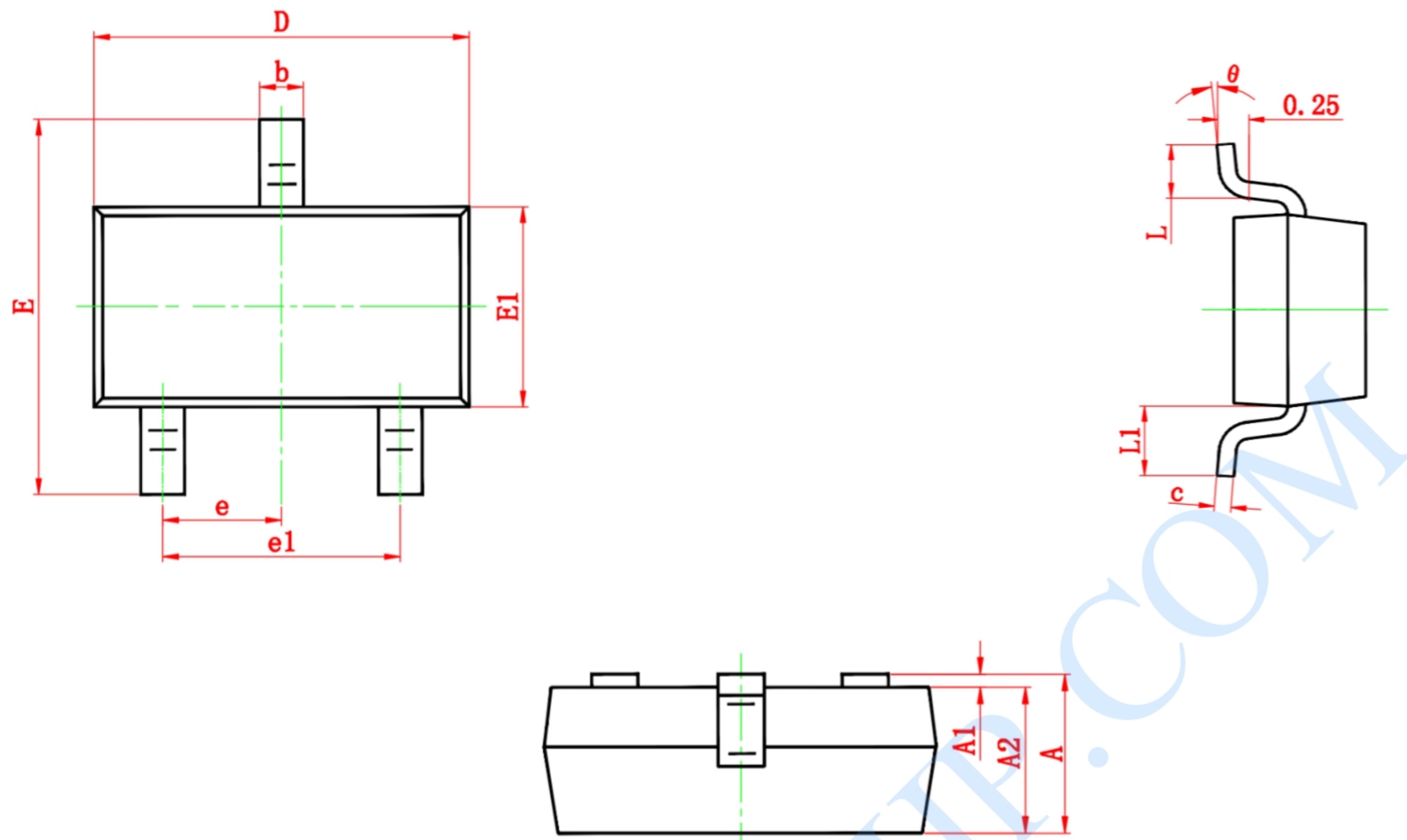
Thermal Characteristics And Typical electrical





PACKAGE DESCRIPTION

SOT23-3L



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	2.250	2.550	0.089	0.100
E1	1.200	1.400	0.047	0.055
e	0.950 TYP.		0.037 TYP.	
e1	1.800	2.000	0.071	0.079
L	0.300	0.500	0.012	0.020
L1	0.550 REF.		0.022 REF.	
θ	0°	8°	0°	8°

Notes

1. All dimensions are in millimeters.
2. Tolerance $\pm 0.10\text{mm}$ (4 mil) unless otherwise specified
3. Package body sizes exclude mold flash and gate burrs. Mold flash at the non-lead sides should be less than 5 mils.
4. Dimension L is measured in gauge plane.
5. Controlling dimension is millimeter, converted inch dimensions are not necessarily exact.



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